

16-Bit, Isolated Sigma-Delta Modulator

Enhanced Product

AD7403-EP

FEATURES

5 MHz to 16 MHz external clock input rate 16 bits, no missing codes Signal-to-noise ratio (SNR): 88 dB typical Effective number of bits (ENOB): 14.2 bits typical Offset drift vs. temperature: 1.6 μV/°C typical On-board digital isolator On-board reference Full-scale analog input range: ±320 mV High common-mode transient immunity: >25 kV/μs Wide-body SOIC with increased creepage package Slew rate limited output for low EMI

Safety and regulatory approvals

UL recognition 5000 V rms for 1 minute per UL 1577 CSA Component Acceptance Notice 5A VDE Certificate of Conformity DIN V VDE V 0884-10 (VDE V 0884-10):2006-12 VIORM = 1250 VPEAK

ENHANCED PRODUCT FEATURES

Defense and aerospace applications (AQEC standard) Military temperature range: -55°C to +125°C Controlled manufacturing baseline One assembly/test site One fabrication site Enhanced product change notification Qualification data available on request

APPLICATIONS

Shunt current monitoring AC motor controls Power and solar inverters Wind turbine inverters Data acquisition systems Analog-to-digital and optoisolator replacements

GENERAL DESCRIPTION

The AD7403-EP¹ is a high performance, second-order, Σ - Δ modulator that converts an analog input signal into a high speed, single-bit data stream, with on-chip digital isolation based on Analog Devices, Inc., *i*Coupler^{*} technology. The device operates from a 5 V (V_{DD1}) power supply and accepts a differential input signal of ±250 mV (±320 mV full-scale). The differential input is ideally suited to shunt voltage monitoring in high voltage applications where galvanic isolation is required.

¹ Protected by U.S. Patents 5,952,849; 6,873,065; and 7,075,329.

Rev. 0

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FUNCTIONAL BLOCK DIAGRAM



The analog input is continuously sampled by a high performance analog modulator, and converted to a ones density digital output stream with a data rate of up to 16 MHz. The original

information can be reconstructed with an appropriate digital filter to achieve 88 dB signal to noise ratio (SNR) at 78.1 kSPS.

The serial interface is digitally isolated. High speed complementary metal oxide semiconductor (CMOS) technology, combined with monolithic transformer technology, means the on-chip isolation provides outstanding performance characteristics, superior to alternatives such as optocoupler devices. The AD7403-EP device is offered in a 16-lead, wide-body SOIC package and has an operating temperature range of -55° C to $+125^{\circ}$ C.

Additional application and technical information can be found in the AD7403 data sheet.

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REVISION HISTORY

4/16—Revision 0: Initial Version

SPECIFICATIONS

 $V_{\rm DD1} = 4.5 \ V \ to \ 5.5 \ V, \\ V_{\rm DD2} = 4.5 \ V \ to \ 5.5 \ V, \\ V_{\rm IN+} = -250 \ mV \ to \ +250 \ mV, \\ V_{\rm IN-} = 0 \ V, \\ T_{\rm A} = -55^{\circ}C \ to \ +125^{\circ}C, \\ f_{\rm MCLKIN} = 5 \ MHz \ to \ 16 \ MHz, \ tested \ NHz \ to \ 16 \ MHz, \ tested \ NHz \ to \ 16 \ MHz, \ tested \ NHz \ to \ 16 \ MHz, \ tested \ NHz \ to \ 16 \ MHz, \ tested \ NHz \ to \ 16 \ MHz, \ tested \ NHz \ to \ 16 \ MHz, \ tested \ NHz \ to \ 16 \ MHz, \ tested \ NHz \ to \ 16 \ MHz, \ tested \ NHz \ to \ 16 \ MHz, \ tested \ NHz \ to \ 16 \ MHz, \ tested \ NHz \ to \ 16 \ MHz, \ tested \ NHz \ to \ 16 \ MHz, \ tested \ NHz \ to \ 16 \ MHz, \ tested \ NHz \ to \ 16 \ MHz, \ tested \ NHz \ to \ 16 \ MHz, \ tested \ NHz \ to \ 16 \ MHz, \ tested \ NHz \ to \ 16 \ MHz, \ tested \ NHz \ to \ 16 \ MHz, \ tested \ NHz \ to \ 16 \ NHz, \ tested \ NHz \ to \ 16 \ NHz \ to \ 16 \ NHz, \ tested \ NHz \ to \ 16 \ NHz \ to \ 16 \ NHz, \ tested \ NHz \ to \ 16 \ NHz, \ tested \ NHz \ to \ 16 \ NHz, \ tested \ NHz \ to \ 16 \ NHz \ to \ 16 \ NHz, \ tested \ NHz \ to \ 16 \ NHz \ to \ NHz \ to \ 1$ with sinc3 filter, 256 decimation rate, as defined by Verilog code, unless otherwise noted. All voltages are relative to their respective ground.

Parameter	Min	Тур	Max	Unit	Test Conditions/Comments
STATIC PERFORMANCE		-76			
Resolution	16			Bits	Filter output truncated to 16 bits
Integral Nonlinearity (INL) ¹	10	±2	±12	LSB	
Differential Nonlinearity (DNL) ¹			±0.99	LSB	Guaranteed no missed codes to 16 bits
Offset Error ¹		±0.2	±0.99	mV	
Offset Drift vs. Temperature ²		1.6	3.8	μV/°C	
onset bint is. temperature		1.3	3.1	μV/°C	0°C to 85°C
Offset Drift vs. V _{DD1} ²		50	5.1	μV/V	
Gain Error ¹		±0.2	±0.95	% FSR	
Gain Error Drift vs. Temperature ²		65	_0.25 95	ppm/°C	
Sum Enor Dine VS. Temperature		40	60	μV/°C	
Gain Error Drift vs. V_{DD1}^2		+0 ±0.6	00	mV/V	
ANALOG INPUT		10.0		1110/0	
Input Voltage Range	-320		+320	mV	Full-scale range
input voltage nange	-250		+320 +250	mV	For specified performance
Input Common-Mode Voltage Range	-230	-200 to +300	7230	mV	ror specified performance
Dynamic Input Current		$-200\ 10\ +300$ ±45	±50		$V_{IN+} = \pm 250 \text{ mV}, V_{IN-} = 0 \text{ V}$
Dynamic input current		±43 0.05	±30	μΑ	$V_{IN+} = \pm 250 \text{ mV}, V_{IN-} = 0 \text{ V}$ $V_{IN+} = 0 \text{ V}, V_{IN-} = 0 \text{ V}$
DC Leakage Current		0.05 ±0.01	106	μΑ	$\mathbf{v}_{\mathrm{IN+}} = 0 \mathbf{v}, \mathbf{v}_{\mathrm{IN-}} = 0 \mathbf{v}$
Input Capacitance		±0.01 14	±0.6	μA	
		14		pF	
	02	07		dله	$V_{IN+} = 1 \text{ kHz}$
Signal-to-Noise-and-Distortion Ratio (SINAD)	82	87		dB	
Signal-to-Noise Ratio (SNR)	86	88		dB	
Total Harmonic Distortion (THD)		-94		dB dB	
Peak Harmonic or Spurious Noise (SFDR)	12.1	-95			
Effective Number of Bits (ENOB) Noise Free Code Resolution	13.1	14.2		Bits	
	14	20		Bits	
	25	30		kV/µs	
LOGIC INPUTS					CMOS with Schmitt trigger
Input Voltage					
High (V _H)	$0.8 \times V_{DD2}$			V	
			$0.2 \times V_{DD2}$	V	
Input Current (I _{IN})			±0.6	μA	
Input Capacitance (C _{IN})			10	pF	
LOGIC OUTPUTS					
Output Voltage					
High (V _{он})	V _{DD2} - 0.1			V	$I_0 = -200 \ \mu A$
Low (V _{OL})			0.4	V	$I_0 = 200 \ \mu A$
POWER REQUIREMENTS					
V _{DD1}	4.5		5.5	V	
V _{DD2}	4.5		5.5	V	
		30	36	mA	$V_{DD1} = 5.5 V$
I _{DD2}		12	18	mA	$V_{DD2} = 5.5 V$
Power Dissipation		231	297	mW	$V_{DD1} = V_{DD2} = 5.5 \text{ V}$

¹ See the Terminology section of the AD7403 datasheet.
² Not production tested. Sample tested during initial release to ensure compliance.

TIMING SPECIFICATIONS

 $V_{DD1} = 4.5 V$ to 5.5 V, $V_{DD2} = 4.5 V$ to 5.5 V, $T_A = -55^{\circ}C$ to $+125^{\circ}C$, unless otherwise noted. Sample tested during initial release to ensure compliance. It is recommended to read MDAT on the MCLKIN rising edge.

Table 2.

	Limit at T _{MIN} , T _{MAX}				
Parameter	Min	Тур	Max	Unit	Description
f _{MCLKIN}	5		16	MHz	Master clock input frequency
t11			45	ns	Data access time after MCLKIN rising edge
t_2^1	12			ns	Data hold time after MCLKIN rising edge
t ₃	$0.45 imes t_{\text{MCLKIN}}$			ns	Master clock low time
t4	$0.45 imes t_{\text{MCLKIN}}$			ns	Master clock high time

¹ Defined as the time required from an 80% MCLKIN input level to when the output crosses 0.8 V or 2.0 V for $V_{DD2} = 3$ V to 3.6 V or when the output crosses 0.8 V or 0.7 × V_{DD2} for $V_{DD2} = 4.5$ V to 5.5 V as outlined in Figure 2. Measured with a ±200 μ A load and a 25 pF load capacitance.



Figure 2. Data Timing

PACKAGE CHARACTERISTICS

Table 3.

Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions/Comments
Resistance (Input to Output) ¹	R _{I-O}		10 ¹²		Ω	
Capacitance (Input to Output) ¹	CI-O		2.2		рF	f = 1 MHz
IC Junction to Ambient Thermal Resistance	ALθ		45		°C/W	Thermocouple located at center of package underside, test conducted on 4-layer board with thin traces

¹ The device is considered a 2-terminal device. For AD7403-EP, Pin 1 to Pin 8 are shorted together and Pin 9 to Pin 16 are shorted together.

INSULATION AND SAFETY RELATED SPECIFICATIONS

Table 4.							
Parameter	Symbol	Value	Unit	Test Conditions/Comments			
Input to Output Momentary Withstand Voltage	VISO	5000 min	V	1 minute duration			
Minimum External Air Gap (Clearance)	L(I01)	8.3 min ^{1, 2}	mm	Measured from input terminals to output terminals, shortest distance through air			
Minimum External Tracking (Creepage)	L(I02)	8.3 min ¹	mm	Measured from input terminals to output terminals, shortest distance path along body			
Minimum Internal Gap (Internal Clearance)		0.034 min	mm	Distance through insulation			
Tracking Resistance (Comparative Tracking Index)	CTI	>400	V	DIN IEC 112/VDE 0303 Part 1 ³			
Isolation Group		Ш		Material Group (DIN VDE 0110, 1/89, Table I) ³			

¹ In accordance with IEC 60950-1 guidelines for the measurement of creepage and clearance distances for a pollution degree of 2 and altitudes <2000 m.

² Consideration must be given to pad layout to ensure the minimum required distance for clearance is maintained. ³ CSA CTI rating for the AD7403-EP is >575 V and therefore Material Group II isolation group.

REGULATORY INFORMATION

Table 5.

UL ¹	CSA	VDE ²
Recognized under 1577 Component Recognition Program ¹	Approved under CSA Component Acceptance Notice 5A	Certified according to DIN V VDE V 0884-10 (VDE V 0884-10):2006-12 ²
5000 V rms Isolation Voltage Single Protection	Basic insulation per CSA 60950-1-07 and IEC 60950-1, 830 V rms (1173 V _{PEAK}), maximum working voltage ³ Reinforced insulation per CSA 60950-1-07 and IEC 60950-1.415 V rms (586 V _{PEAK}) maximum working voltage ³	Reinforced insulation per DIN V VDE V 0884-10 (VDE V 0884-10):2006-12, 1250 V _{PEAK}
	Reinforced insulation per IEC 60601-1, 250 V rms (353 V _{PEAK}) maximum working voltage	
File E214100	File 205078	File 2471900-4880-0001

¹ In accordance with UL 1577, each AD7403-EP is proof tested by applying an insulation test voltage \geq 6000 V rms for 1 second (current leakage detection limit = 15 μ A). ² In accordance with DIN V VDE V 0884-10, each AD7403-EP is proof tested by applying an insulation test voltage ≥ 2344 V_{FEAK} for 1 second (partial discharge detection limit = 5 pC).

³ Rating is calculated for a pollution degree of 2 and a Material Group III. The AD7403-EP RI-16-2 package material is rated by CSA to a CTI of >575 V and therefore Material Group II.

DIN V VDE V 0884-10 (VDE V 0884-10):2006-12 INSULATION CHARACTERISTICS

This isolator is suitable for reinforced electrical isolation only within the safety limit data. Maintenance of the safety data is ensured by means of protective circuits.

Table 6.	1	T	
Description	Symbol	Characteristic	Unit
INSTALLATION CLASSIFICATION PER DIN VDE 0110			
For Rated Mains Voltage ≤300 V rms		I to IV	
For Rated Mains Voltage ≤450 V rms		I to IV	
For Rated Mains Voltage ≤600 V rms		l to IV	
For Rated Mains Voltage ≤1000 V rms		l to IV	
CLIMATIC CLASSIFICATION		40/105/21	
POLLUTION DEGREE (DIN VDE 0110, TABLE 1)		2	
MAXIMUM WORKING INSULATION VOLTAGE	VIORM	1250	VPEAK
INPUT TO OUTPUT TEST VOLTAGE, METHOD B1			
$V_{IORM} \times 1.875 = V_{PR}$, 100% Production Test, $t_m = 1$ Second, Partial Discharge < 5 pC	V _{PD(M)}	2344	VPEAK
INPUT TO OUTPUT TEST VOLTAGE, METHOD A	V _{PR(M)}		
After Environmental Test Subgroup 1			
$V_{IORM} \times 1.6 = V_{PR}$, $t_m = 60$ Seconds, Partial Discharge < 5 pC		2000	VPEAK
After Input and/or Safety Test Subgroup 2/ Safety Test Subgroup 3			
$V_{IORM} \times 1.2 = V_{PR}$, $t_m = 60$ Seconds, Partial Discharge < 5 pC		1500	VPEAK
HIGHEST ALLOWABLE OVERVOLTAGE (TRANSIENT OVERVOLTAGE, t _{TR} = 10 Seconds)	VIOTM	8000	VPEAK
SURGE ISOLATION VOLTAGE	VIOSM		VPEAK
1.2 μs Rise Time, 50 μs, 50% Fall Time		7500	VPEAK
SAFETY LIMITING VALUES (MAXIMUM VALUE ALLOWED IN THE EVENT OF A FAILURE, SEE Figure 3)			
Case Temperature	Ts	150	°C
Side 1 (Pvdd1) and Side 2 (Pvdd2) Power Dissipation	Pso	2.78	W
INSULATION RESISTANCE AT $T_{s_1} V_{10} = 500 V$	RIO	>109	Ω



Figure 3. Thermal Derating Curve, Dependence of Safety Limiting Values with Case Temperature per DIN V VDE V 0884-10

ABSOLUTE MAXIMUM RATINGS

 $T_A = 25^{\circ}$ C, unless otherwise noted. All voltages are relative to their respective ground.

Table 7.

Parameter	Rating
V _{DD1} to GND ₁	–0.3 V to +6.5 V
V _{DD2} to GND ₂	–0.3 V to +6.5 V
Analog Input Voltage to GND1	-1 V to V _{DD1} + 0.3 V
Digital Input Voltage to GND ₂	-0.3 V to V _{DD2} + 0.5 V
Output Voltage to GND ₂	$-0.3V$ to V_{DD2} + 0.3 V
Input Current to Any Pin Except Supplies ¹	±10 mA
Operating Temperature Range	–55°C to +125°C
Storage Temperature Range	–65°C to +150°C
Junction Temperature	150°C
Pb-Free Temperature, Soldering	
Reflow	260°C
ESD	2 kV
FICDM ²	±1250 V
HBM ³	±4000 V

¹ Transient currents of up to 100 mA do not cause SCR to latch up.

² JESD2-C101; RC network: 1 Ω, Cpkg; Class: IV.
³ ESDA/JEDEC JS-001-2011; RC network: 1.5 kΩ, 100 pF; Class: 3A.

Stresses at or above those listed under Absolute Maximum Ratings may cause permanent damage to the product. This is a stress rating only; functional operation of the product at these or any other conditions above those indicated in the operational section of this specification is not implied. Operation beyond the maximum operating conditions for extended periods may affect product reliability.

Table 8. Maximum Continuous Working Voltage¹

Table 6. Maximum Continuous working voltage						
Parameter	Max	Unit	Constraint			
AC Voltage						
Bipolar Waveform	1250	Vpeak	20-year minimum lifetime (VDE approved working voltage)			
Unipolar Waveform	1250	V _{PEAK}	20-year minimum lifetime			
DC Voltage	1250	Vpeak	20-year minimum lifetime			

¹ Maximum continuous working voltage refers to continuous voltage magnitude imposed across the isolation barrier.

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

AD7403-EP

PIN CONFIGURATIONS AND FUNCTION DESCRIPTIONS



Figure 4. Pin Configuration

Table 9. Pin Function Descriptions

Pin No.	Mnemonic	Description
1, 7	V _{DD1}	Supply Voltage, 4.5 V to 5.5 V. This is the supply voltage for the isolated side of the AD7403-EP and is relative to GND ₁ . For device operation, connect the supply voltage to both Pin 1 and Pin 7. Decouple each supply pin to GND ₁ with a 10 μ F capacitor in parallel with a 1 nF capacitor.
2	V _{IN+}	Positive Analog Input.
3	V _{IN-}	Negative Analog Input. Normally connected to GND ₁ .
4, 8	GND ₁	Ground 1. This pin is the ground reference point for all circuitry on the isolated side.
5, 6	NIC	Not Internally Connected. These pins are not internally connected. Connect to V _{DD1} , GND1, or leave floating.
9, 16	GND ₂	Ground 2. This pin is the ground reference point for all circuitry on the nonisolated side.
10, 12, 15	NIC	Not Internally Connected. These pins are not internally connected. Connect to V _{DD2} , GND ₂ , or leave floating.
11	MDAT	Serial Data Output. The single bit modulator output is supplied to this pin as a serial data stream. The bits are clocked out on the rising edge of the MCLKIN input and are valid on the following MCLKIN rising edge.
13	MCLKIN	Master Clock Logic Input. 5 MHz to 20 MHz frequency range. The bit stream from the modulator is propagated on the rising edge of the MCLKIN.
14	V _{DD2}	Supply Voltage, 3 V to 5.5 V. This is the supply voltage for the nonisolated side and is relative to GND ₂ . Decouple this supply to GND ₂ with a 100 nF capacitor.

TYPICAL PERFORMANCE CHARACTERISTICS

 $T_A = 25^{\circ}$ C, $V_{DD1} = 5$ V, $V_{DD2} = 5$ V, $V_{IN+} = -250$ mV to +250 mV, $V_{IN-} = 0$ V, $f_{MCLKIN} = 16$ MHz, using a sinc3 filter with a 256 oversampling ratio (OSR), unless otherwise noted.

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AD7403-EP

Enhanced Product



Figure 16. IDD1 vs. VDD1 at Various Temperatures and Clock Rates

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Figure 17. IDD1 vs. VIN+ DC Input at Various Temperatures



Figure 18. IDD2 vs. VDD2 at Various Temperatures and Clock Rates







Figure 20. I_{IN+} vs. V_{IN+} DC Input at Various Clock Rates

AD7403-EP

OUTLINE DIMENSIONS



ORDERING GUIDE

Model ¹	Temperature Range	Package Description	Package Option
AD7403TRIZ-EP	-55°C to +125°C	16-Lead Standard Small Outline Package, with Increased Creepage [SOIC_IC]	RI-16-2
AD7403TRIZ-EP-RL7	–55°C to +125°C	16-Lead Standard Small Outline Package, with Increased Creepage [SOIC_IC]	RI-16-2
EVAL-AD7403FMCZ		AD7403 Evaluation Board	
EVAL-SDP-CH1Z		System Demonstration Platform	

 1 Z = RoHS Compliant Part.

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